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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

### Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I <sup>2</sup> C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	83
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	16К х 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151vet7

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• **Stop** mode without RTC

Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, LSE and HSE crystal oscillators are disabled. The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 8  $\mu$ s. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB wakeup.

• **Standby** mode with RTC

Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire  $V_{CORE}$  domain is powered off. The PLL, MSI RC, HSI RC and HSE crystal oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC\_CSR).

The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

• Standby mode without RTC

Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire  $V_{CORE}$  domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC\_CSR).

The device exits Standby mode in 60  $\mu$ s when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

*Note:* The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

	Functionalities depending on the operating power supply range							
Operating power supply range	DAC and ADC operation	USB	Dynamic voltage scaling range	I/O operation				
V <sub>DD</sub> = V <sub>DDA</sub> = 1.65 to 1.71 V	Not functional	Not functional	Range 2 or Range 3	Degraded speed performance				
$V_{DD} = V_{DDA} = 1.71 \text{ to } 1.8 \text{ V}^{(1)}$	Not functional	Not functional	Range 1, Range 2 or Range 3	Degraded speed performance				
V <sub>DD</sub> =V <sub>DDA</sub> = 1.8 to 2.0 V <sup>(1)</sup>	Conversion time up to 500 Ksps	Not functional	Range 1, Range 2 or Range 3	Degraded speed performance				

### Table 3. Functionalities depending on the operating power supply range



# 3.7 Memories

The STM32L151xE and STM32L152xE devices have the following features:

- 80 Kbytes of embedded RAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
  - 512 Kbytes of embedded Flash program memory
  - 16 Kbytes of data EEPROM
  - Options bytes

Flash program and data EEPROM are divided into two banks, this enables writing in one bank while running code or reading data in the other bank.

The options bytes are used to write-protect or read-out protect the memory (with 4 Kbytes granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (ARM Cortex-M3 JTAG and serial wire) and boot in RAM selection disabled (JTAG fuse)

The whole non-volatile memory embeds the error correction code (ECC) feature.

# 3.8 DMA (direct memory access)

The flexible 12-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI,  $I^2C$ , USART, general-purpose timers, DAC and ADC.



### 3.17.3 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The SPIs can be served by the DMA controller.

# 3.17.4 Inter-integrated sound (I<sup>2</sup>S)

Two standard I2S interfaces (multiplexed with SPI2 and SPI3) are available. They can operate in master or slave mode, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I2S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

The I2Ss can be served by the DMA controller.

### 3.17.5 Universal serial bus (USB)

The STM32L151xE and STM32L152xE devices embed a USB device peripheral compatible with the USB full-speed 12 Mbit/s. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and supports suspend/resume. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).

# 3.18 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.



# 3.19 Development support

### 3.19.1 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG JTMS and JTCK pins are shared with SWDAT and SWCLK, respectively, and a specific sequence on the JTMS pin is used to switch between JTAG-DP and SW-DP.

The JTAG port can be permanently disabled with a JTAG fuse.

### 3.19.2 Embedded Trace Macrocell™

The ARM<sup>®</sup> Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32L151xE and STM32L152xE device through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.



# 4 Pin descriptions





Na	me	Abbreviation Definition						
No	tes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset						
i	Alternate functions	Functions select	ted through GPIOx_AFR registers					
Pin functions	Additional functions	Functions direct	ly selected/enabled through peripheral registers					

 Table 7. Legend/abbreviations used in the pinout table (continued)

### Table 8. STM32L151xE and STM32L152xE pin definitions

		Pins							Pin functions					
LQFP144	UFBGA132	LQFP100	LQFP64	WLCSP104	Pin name	Pin Type <sup>(1)</sup>	I / O structure	Additional functions						
1	B2	1	-	D6	PE2	I/O	FT	PE2	TIM3_ETR/LCD_SEG38/ TRACECLK	-				
2	A1	2	-	D7	PE3	PE3 I/O FT PE3 TIM3_CH1/LCD_SEG39/ TRACED0		-						
3	B1	3	-	C8	PE4	I/O	FT	PE4	TIM3_CH2/TRACED1	-				
4	C2	4	-	B9	PE5	I/O	FT	PE5	TIM9_CH1/TRACED2	-				
5	D2	5	-	E6	PE6- WKUP3	I/O	FT	PE6	TIM9_CH2/TRACED3	WKUP3/ RTC_TAMP3				
6	E2	6	1	E7	V <sub>LCD</sub> <sup>(3)</sup>	S	-	V <sub>LCD</sub>	-	-				
7	C1	7	2	C9	PC13-WKUP2	PC13-WKUP2 I/O FT PC13 -		-	WKUP2/RTC_TA MP1/RTC_TS/ RTC_OUT					
8	D1	8	3	D8	PC14- OSC32_IN <sup>(4)</sup>	C14- 32_IN <sup>(4)</sup> I/O TC PC14 -		OSC32_IN						
9	E1	9	4	D9	PC15- OSC32_OUT	I/O	тс	PC15	-	OSC32_OUT				
10	D6	-	-	-	PF0	I/O	I/O FT PF0 -		-					
11	D5	-	-	-	PF1	PF1 I/O FT PF1 -		-						
12	D4	-	-	-	PF2	I/O	FT	PF2	-	-				
13	E4	-	-	-	PF3	I/O	FT	PF3	-	-				
14	F3	-	-	-	PF4	I/O	FT	PF4	-	-				
15	F4	-	-	-	PF5	I/O		PF5	-	-				



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	1		Ta	ble 9. Alte	rnate fu	nction inp	out/outpu	t (continued	l)					
		Digital alternate function number												
_	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	•	AFIO11	•	AFIO14	AFIO15
Port name						Alterna	te functio	n						
	SYSTEM	TIM2	TIM3/4/ 5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/ 3	UART4/ 5	-	LCD	-	CPRI	SYSTEM
PE2	TRACECK	-	TIM3_ETR	-	-	-	-	-	-	-	SEG 38	-	TIMx_IC3	EVENT OUT
PE3	TRACED0	-	TIM3_CH1	-	-	-	-	-	-	-	SEG 39	-	TIMx_IC4	EVENT OUT
PE4	TRACED1	-	TIM3_CH2	-	-	-	-	-	-	-	-	-	TIMx_IC1	EVENT OUT
PE5	TRACED2	-	-	TIM9_CH1	-	-	-	-	-	-	-	-	TIMx_IC2	EVENT OUT
PE6- WKUP3	TRACED3	-	-	TIM9_CH2	-	-	-	-	-	-	-	-	TIMx_IC3	EVENT OUT
PE7	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC4	EVENT OUT
PE8	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC1	EVENT OUT
PE9	-	TIM2_CH1_ ETR	-	-	-	-	-	-	-	-	-	-	TIMx_IC2	EVENT OUT
PE10	-	TIM2_CH2	-	-	-	-	-	-	-	-	-	-	TIMx_IC3	EVENT OUT
PE11	-	TIM2_CH3	-	-	-	-	-	-	-	-	-	-	TIMx_IC4	EVENT OUT
PE12	-	TIM2_CH4	-	-	-	SPI1_NSS	-	-	-	-	-	-	TIMx_IC1	EVENT OUT
PE13	-	-	-	-	-	SPI1_SCK	-	-	-	-	-	-	TIMx_IC2	EVENT OUT
PE14	-	-	-	-	-	SPI1_MISO	-	-	-	-	-	-	TIMx_IC3	EVENT OUT
PE15	-	-	-	-	-	SPI1_MOSI	-	-	-	-	-	-	TIMx_IC4	EVENT OUT

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			Tal	ble 9. Alte	rnate fur	nction inp	out/outpu	t (continued	I)					
		Digital alternate function number												
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	•	AFIO11	•	AFIO14	AFIO15
Port name		Alternate function												
	SYSTEM	TIM2	TIM3/4/ 5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/ 3	UART4/ 5	-	LCD	-	CPRI	SYSTEM
PG12	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PG13	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PG14	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PG15	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PH0OSC_IN	-	-	-	-	-	-	-	-	-	-	-	-	-	-
PH1OSC_OUT	-	-	-	-	-	-	-	-	-	-	-	-	-	-
PH2	-	-	-	-	-	-	-	-	-	-	-	-	-	-

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# 5 Memory mapping



Figure 8. Memory map



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Figure 16. HSE oscillator circuit diagram

1. R<sub>EXT</sub> value depends on the crystal characteristics.

### Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 29*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>LSE</sub>	Low speed external oscillator frequency	-	-	32.768	-	kHz
R <sub>F</sub>	Feedback resistor	-	-	1.2	-	MΩ
C <sup>(2)</sup>	Recommended load capacitance versus equivalent serial resistance of the crystal $(R_S)^{(3)}$	R <sub>S</sub> = 30 kΩ	-	8	-	pF
I <sub>LSE</sub>	LSE driving current	$V_{DD}$ = 3.3 V, $V_{IN}$ = $V_{SS}$	-	-	1.1	μA
		V <sub>DD</sub> = 1.8 V	-	450	-	
I <sub>DD (LSE)</sub>	LSE oscillator current consumption	V <sub>DD</sub> = 3.0 V	-	600	-	nA
		V <sub>DD</sub> = 3.6V		750	-	
g <sub>m</sub>	Oscillator transconductance	-	3	-	-	μA/V
t <sub>SU(LSE)</sub> <sup>(4)</sup>	Startup time	V <sub>DD</sub> is stabilized	-	1	-	S

Table 29. LSE	oscillator	characteristics	$(f_{LSE} =$	32.768	kHz) <sup>(1)</sup>
---------------	------------	-----------------	--------------	--------	---------------------

1. Guaranteed by characterization results.

2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".

 The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R<sub>S</sub> value for example MSIV-TIN32.768kHz. Refer to crystal manufacturer for more details.



- t<sub>SU(LSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.
- Note: For  $C_{L1}$  and  $C_{L2}$ , it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator (see Figure 17).  $C_{L1}$  and  $C_{L2}$ , are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of  $C_{L1}$  and  $C_{L2}$ .

Load capacitance  $C_L$  has the following formula:  $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$  where  $C_{stray}$  is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

**Caution:** To avoid exceeding the maximum value of  $C_{L1}$  and  $C_{L2}$  (15 pF) it is strongly recommended to use a resonator with a load capacitance  $C_L \leq 7$  pF. Never use a resonator with a load capacitance of 12.5 pF.

**Example:** if the user chooses a resonator with a load capacitance of  $C_L = 6 \text{ pF}$  and  $C_{stray} = 2 \text{ pF}$ , then  $C_{L1} = C_{L2} = 8 \text{ pF}$ .



#### Figure 17. Typical application with a 32.768 kHz crystal

1. Guaranteed by characterization results.

### Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105$ °C conforming to JESD78A	II level A

### 6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below  $V_{SS}$  or above  $V_{DD}$  (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

### Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of  $-5 \mu$ A/+0  $\mu$ A range), or other functional failure (for example reset occurrence oscillator frequency deviation, LCD levels).

The test results are given in the Table 41.

		Functional s	Unit	
Symbol	Description	Negative Positive injection injectio		
I <sub>INJ</sub>	Injected current on all 5 V tolerant (FT) pins	-5 <sup>(1)</sup>	NA	
	Injected current on BOOT0	-0	NA	mA
	Injected current on any other pin	-5 <sup>(1)</sup>	+5	

1. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.



## 6.3.16 Communications interfaces

## I<sup>2</sup>C interface characteristics

The device I<sup>2</sup>C interface meets the requirements of the standard I<sup>2</sup>C communication protocol with the following restrictions: SDA and SCL are not "true" open-drain I/O pins. When configured as open-drain, the PMOS connected between the I/O pin and V<sub>DD</sub> is disabled, but is still present.

The I<sup>2</sup>C characteristics are described in *Table 47*. Refer also to *Section 6.3.13: I/O port characteristics* for more details on the input/output ction characteristics (SDA and SCL).

Symbol	Parameter	Standard mode I <sup>2</sup> C <sup>(1)(2)</sup>		Fast mode I <sup>2</sup> C <sup>(1)(2)</sup>		Unit	
		Min	Max	Min	Мах		
t <sub>w(SCLL)</sub>	SCL clock low time	4.7	-	1.3	-		
t <sub>w(SCLH)</sub>	SCL clock high time	4.0	-	0.6	-	μο	
t <sub>su(SDA)</sub>	SDA setup time	250	-	100	-		
t <sub>h(SDA)</sub>	SDA data hold time	-	3450 <sup>(3)</sup>	-	900 <sup>(3)</sup>		
t <sub>r(SDA)</sub> t <sub>r(SCL)</sub>	SDA and SCL rise time	-	1000	-	300	ns	
t <sub>f(SDA)</sub> t <sub>f(SCL)</sub>	SDA and SCL fall time	DA and SCL fall time - 300 -		300			
t <sub>h(STA)</sub>	Start condition hold time	4.0	-	0.6	-		
t <sub>su(STA)</sub>	Repeated Start condition setup time         4.7         -		-	0.6	-	μs	
t <sub>su(STO)</sub>	Stop condition setup time	4.0	-	0.6	-	μs	
t <sub>w(STO:STA)</sub>	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs	
Cb	Capacitive load for each bus line	-	400	-	400	pF	
t <sub>SP</sub>	Pulse width of spikes that are suppressed by the analog filter	0	50 <sup>(4)</sup>	0	50 <sup>(4)</sup>	ns	

Table 47. I<sup>2</sup>C characteristics

1. Guaranteed by design.

 f<sub>PCLK1</sub> must be at least 2 MHz to achieve standard mode I<sup>2</sup>C frequencies. It must be at least 4 MHz to achieve fast mode I<sup>2</sup>C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I<sup>2</sup>C fast mode clock.

3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

4. The minimum width of the spikes filtered by the analog filter is above t<sub>SP(max)</sub>.



### **SPI characteristics**

Unless otherwise specified, the parameters given in the following table are derived from tests performed under the conditions summarized in *Table 13*.

Refer to *Section 6.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Symbol	Parameter	Conditions	Min	Max <sup>(2)</sup>	Unit
_		Master mode	-	16	
f <sub>SCK</sub>	SPI clock frequency	Slave mode	-	16	MHz
		Slave transmitter	-	12 <sup>(3)</sup>	
$t_{r(SCK)}^{(2)}$ $t_{f(SCK)}^{(2)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	6	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
t <sub>su(NSS)</sub>	NSS setup time	Slave mode	4t <sub>HCLK</sub>	-	
t <sub>h(NSS)</sub>	NSS hold time	Slave mode	2t <sub>HCLK</sub>	-	
t <sub>w(SCKH)</sub> <sup>(2)</sup> t <sub>w(SCKL)</sub> <sup>(2)</sup>	SCK high and low time	Master mode	t <sub>SCK</sub> /2-5	t <sub>SCK</sub> /2+3	
t <sub>su(MI)</sub> <sup>(2)</sup>	Data input actus timo	Master mode	5	-	
t <sub>su(SI)</sub> <sup>(2)</sup>		Slave mode	6	-	
t <sub>h(MI)</sub> <sup>(2)</sup>	Data input hold time	Master mode	5	-	ns
t <sub>h(SI)</sub> <sup>(2)</sup>		Slave mode	5	-	
t <sub>a(SO)</sub> <sup>(4)</sup>	Data output access time	Slave mode	0	3t <sub>HCLK</sub>	
t <sub>v(SO)</sub> (2)	Data output valid time	Slave mode	-	33	
t <sub>v(MO)</sub> <sup>(2)</sup>	Data output valid time	Master mode	-	6.5	
t <sub>h(SO)</sub> <sup>(2)</sup>	Data output hold time	Slave mode	17	-	
t <sub>h(MO)</sub> <sup>(2)</sup>		Master mode	0.5	-	

Table 49. SPI characteristics<sup>(1)</sup>

1. The characteristics above are given for voltage range 1.

2. Guaranteed by characterization results.

3. The maximum SPI clock frequency in slave transmitter mode is given for an SPI slave input clock duty cycle (DuCy(SCK)) ranging between 40 to 60%.

4. Min time is for the minimum time to drive the output and max time is for the maximum time to validate the data.



### 6.3.22 LCD controller

The device embeds a built-in step-up converter to provide a constant LCD reference voltage independently from the V<sub>DD</sub> voltage. An external capacitor C<sub>ext</sub> must be connected to the V<sub>LCD</sub> pin to decouple this converter.

Symbol	Parameter		Тур	Max	Unit
$V_{LCD}$	LCD external voltage	-	-	3.6	
$V_{LCD0}$	LCD internal reference voltage 0	-	2.6	-	
V <sub>LCD1</sub>	LCD internal reference voltage 1	-	2.73	-	
V <sub>LCD2</sub>	LCD internal reference voltage 2	-	2.86	-	
$V_{LCD3}$	LCD internal reference voltage 3	-	2.98	-	V
$V_{LCD4}$	LCD internal reference voltage 4	-	3.12	-	
$V_{LCD5}$	LCD internal reference voltage 5	-	3.26	-	
V <sub>LCD6</sub>	LCD internal reference voltage 6	-	3.4	-	
V <sub>LCD7</sub>	LCD internal reference voltage 7	-	3.55	-	
C <sub>ext</sub>	V <sub>LCD</sub> external capacitance	0.1	-	2	μF
. (1)	Supply current at V <sub>DD</sub> = 2.2 V	-	3.3	-	
LCD,	Supply current at V <sub>DD</sub> = 3.0 V	-	3.1	-	μΑ
R <sub>Htot</sub> <sup>(2)</sup>	Low drive resistive network overall value	5.28	6.6	7.92	MΩ
$R_L^{(2)}$	High drive resistive network total value	192	240	288	kΩ
V <sub>44</sub>	Segment/Common highest level voltage	-	-	V <sub>LCD</sub>	V
V <sub>34</sub>	Segment/Common 3/4 level voltage	-	3/4 V <sub>LCD</sub>	-	
V <sub>23</sub>	Segment/Common 2/3 level voltage	-	2/3 V <sub>LCD</sub>	-	
V <sub>12</sub>	Segment/Common 1/2 level voltage	-	$1/2 V_{LCD}$	-	V
V <sub>13</sub>	Segment/Common 1/3 level voltage	-	$1/3 V_{LCD}$	-	v
V <sub>14</sub>	Segment/Common 1/4 level voltage - 1/4 V <sub>LCD</sub>		-		
V <sub>0</sub>	Segment/Common lowest level voltage	0	-	-	
$\Delta Vxx^{(3)}$	Segment/Common level voltage error T <sub>A</sub> = -40 to 105 $^{\circ}$ C	-	-	±50	mV

### Table 64. LCD controller characteristics

1. LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected.

2. Guaranteed by design.

3. Guaranteed by characterization results.



	data					
Symbol	millimeters		inches <sup>(1)</sup>			
	Min	Тур	Мах	Min	Тур	Мах
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
CCC	-	-	0.080	-	-	0.0031

# Table 65. LQFP144, 20 x 20 mm, 144-pin low-profile quad flat package mechanical

1. Values in inches are converted from mm and rounded to 4 decimal digits.



# 7.5 WLCSP104, 0.4 mm pitch wafer level chip scale package information



1. Drawing is not to scale.



# 9 Revision History

Date	Revision	Changes
31-Oct-2013	1	Initial release.
		Added Input Voltage in Table 13: General operating conditions Updated: Chapter 2.2: Ultra-low-power device continuum, Table 13: General operating conditions, Table 28: Current consumption in Low- power run mode, Table 21: Current consumption in Low-power sleep mode, Table 48: Flash memory and data EEPROM endurance and retention, Table 77: ADC characteristics, Table 78: ADC accuracy Updated Ultra-Low-power Feature inside Cover Page
19-Feb-2014	2	Updated: Table 28: Current consumption in Low-power run mode, Table 21: Current consumption in Low-power sleep mode, Table 22: Typical and maximum current consumptions in Stop mode, Table 23: Typical and maximum current consumptions in Standby mode, Table 38: High-speed external user clock characteristics, Figure 12: High-speed external clock source AC timing diagram, Table 39: Low- speed external user clock characteristics, Figure 13: Low-speed external clock source AC timing diagram, Table 78: ADC accuracy, Table 57: EMS characteristics, Table 58: EMI characteristics, Table 59: ESD absolute maximum ratingsTable 60: Electrical sensitivities, Table 63: I/O static characteristics, Table 66: NRST pin characteristics. Added WLCSP104, 0.4 mm pitch wafer level chip scale package recommended footprint for package WLCSP104, removed figures "Power supply and reference decoupling (V <sub>REF+</sub> not connected to V <sub>DDA</sub> ) and "Power supply and reference decoupling (V <sub>REF+</sub>
21-Feb-2014	3	Ultra low power features modification inside Cover page. Updated Table 4: Functionalities depending on the working mode (from Run/active down to standby), Table 80: DAC characteristics
16-May-2014	4	Updated I <sub>IO</sub> in <i>Table 11: Current characteristics</i> . Removed note 4 in <i>Table 61: Temperature sensor characteristics</i> . Added <i>Table 41: UFBGA132, 7 x 7 mm, 132-ball ultra thin, fine-pitch ball grid array package recommended footprint</i> Modified pins F9 for WLCSP104 package inside <i>Table 8:</i> <i>STM32L151xE and STM32L152xE pin definitions</i>
13-Oct-2014	5	Updated Section 3.17: Communication interfaces putting I2S characteristics inside. Updated DMIPS features in cover page and Section 2: Description. Updated max temperature at 105°C instead of 85°C in the whole datasheet. Updated current consumption in Table 19: Current consumption in Sleep mode. Updated Table 24: Peripheral current consumption with new measured current values. Updated Table 57: Maximum source impedance RAIN max adding note 2.

### Table 73. Document revision history

